

DESCRIPTION

The 2SA1362-Y & 2SA1362-G are available in SOT-23 package.

ORDERING INFORMATION

Package Type	Part Number		
COT 22	2SA1362-Y		
SOT-23	2SA1362-G		
SPQ	3,000pcs/Reel		
AiT provides all RoHS Compliant Products			

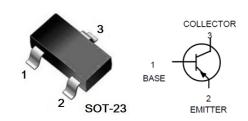
h_{FE} CLASSIFICATION

Rank	Range	
Υ	120 ~ 240	
G	200 ~ 400	

PIN DESCRIPTION

- · Suitable for the driver stage of small motors.
- Small Package

PIN DESCRIPTION



PIN#	DESCRIPTION		
1	Base		
2	Emitter		
3	Collector		

ABSOLUTE MAXIMUM RATINGS

T_A = 25°C, unless otherwise specified.

V _{CBO} , Collector-Base Voltage	-15 V
V _{CEO} , Collector-Emitter Voltage	-15 V
V _{EBO} , Emitter-Base Voltage	-5 V
Ic, Collector Current	-800 mA
I _B , Base Current	-160 mA
P _C , Collector Dissipation	200 mW
T _J , Junction Temperature	150 °C
T _{stg} , Storage Temperature	-55 ~ +150 °C

Stresses above may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated in the Electrical Characteristics are not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

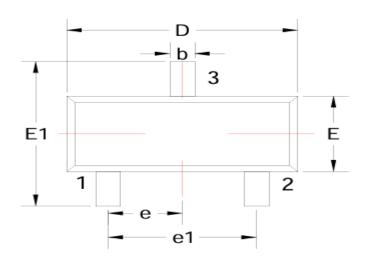
ELECTRICAL CHARACTERISTICS

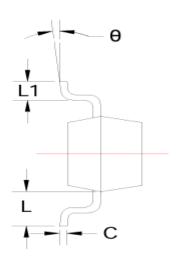
 T_A =25°C unless otherwise specified.

Parameter	Symbols	Conditions	Min.	Тур.	Max.	Unit
Collector Cut-off Current	Ісво	V _{CB} = -15 V, I _E = 0	-	1	-100	nA
Emitter Cut-off Current	I _{EBO}	V _{EB} = -5 V, I _C = 0	-	-	-100	nA
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	I _C = -10 mA, I _B = 0	-15	-	-	V
DC Current Gain	h _{FE}	V _{CE} = -1 V, I _C = -100 mA	120	-	400	1
Collector-Emitter Saturation Voltage	V _{CE} (sat)	I_{C} = -400 mA, I_{B} = -8 mA,	-	-	-0.2	V
Base-Emitter Voltage	V _{BE}	$V_{CE} = -1 V$, $I_{C} = -10 \text{ mA}$	-0.5	-	-0.8	V
Transition Frequency	f⊤	$V_{CE} = -5 \text{ V},$ $I_{C} = -10 \text{ mA}$	-	120	1	MHz
Collector Output Capacitance	Cob	$V_{CB} = -10 \text{ V},$ $I_E = 0, f=1 \text{Mhz}$	-	13	-	pF

PACKAGE INFORMATION

Dimension in SOT-23 (Unit: mm)







Comple ed	Millir	neter	
Symbol	Min.	Max.	
Α	0.900	1.150	
A1	0.900	1.050	
b	0.300	0.500	
С	0.080	0.150	
D	2.800	3.000	
E	1.200	1.400	
E1	2.250	2.550	
е	0.950 TYP.		
e1	1.800	2.000	
L	0.550 REF		
L1	0.300	0.500	
θ	0°	8°	

2SA1362
TRANSISTOR
SILICON PNP EPITAXIAL TYPE TRANSISTOR

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